SCT4026DRHR



Automotive Grade N-channel SiC power MOSFET

Datasheet

V_{DSS}	750V
R _{DS(on)} (Typ.)	26mΩ
I _D ^{*1}	56A
P_D	176W

●Outline TO-247-4L (1)(2)(3)(4)

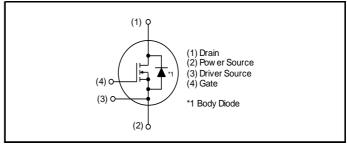
Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating; RoHS compliant

Application

- Automobile
- Switch mode power supplies

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Taping code	C15
	Marking	SCT4026DR

● Absolute maximum ratings (T_c = 25°C)

Parameter		Symbol	Value	Unit
Drain - source voltage		V_{DSS}	750	V
Continuous drain and source current	\/ -\/	, , *1	56	А
$T_c = 100$ °C	$V_{GS} = V_{GS_on}$	I _D , I _S *1	39	А
Pulsed drain current	$V_{GS} = V_{GS_on}$	l _{D,pulse} *2	91	Α
Body diode pulsed forward current	$V_{GS} = 0 V$	I _{S,pulse} *3	56	Α
Body diode surge forward current	$V_{GS} = 0 V$	I _{S,pulse} *4	91	А
Gate - source voltage (DC)		V_{GSS_DC}	-4 to +21	V
Gate - source surge voltage (t _{surge} < 300ns)		$V_{\rm GSS_surge}^{*5}$	-4 to +23	V
Recommended turn-on gate - source drive voltage		${\sf V_{GS_on}}^{*6}$	+15 to +18	V
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V
Virtual junction temperature		T_{vj}	175	°C
Range of storage temperature		T_{stg}	-40 to +175	°C

ullet Electrical characteristics ($T_{vj} = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions		Values		Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown	W	$V_{GS} = 0 \text{ V}, I_D = 9.2 \text{mA}$				V
voltage	$V_{(BR)DSS}$	$T_{vj} = 25^{\circ}C$	750	-	-	V
		$V_{GS} = 0 \text{ V}, V_{DS} = 750 \text{V}$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	80	μA
Diam current		T _{vj} = 150°C	-	10	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V$, $V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -4V$, $V_{DS} = 0V$	ı	ı	-100	nA
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_{D} = 15.4 \text{mA}$	2.8	ı	4.8	V
		$V_{GS} = 18V, I_{D} = 29A$				
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	26	34	mΩ
		T _{vj} = 150°C		44		
Gate input resistance	R_{G}	f = 1MHz, open drain	-	1	-	Ω

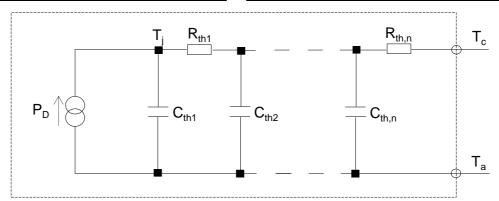
●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R _{thJC} *9	-	0.65	0.85	K/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.1 ×10 ⁻¹	
R _{th2}	2.5 ×10 ⁻¹	K/W
R_{th3}	2.9 ×10 ⁻¹	

Symbol	Value	Unit
C _{th1}	5.8 ×10 ⁻⁴	
C _{th2}	2.3 ×10 ⁻³	Ws/K
C _{th3}	1.1 ×10 ⁻²	



Electrical characteristics ($T_{vj} = 25$ °C unless otherwise specified)

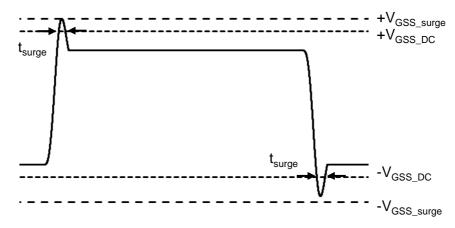
Doromotor	Cymbol	Symbol Conditions -	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g _{fs} *8	$V_{DS} = 10V, I_{D} = 29A$	-	16	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	2320	ı	
Output capacitance	C _{oss}	V _{DS} = 500V	-	111	•	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	9	ı	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	143	ı	pF
Total Gate charge	Q _g *8	$V_{DS} = 500V$ $I_{D} = 29A$	-	94	ı	
Gate - Source charge	Q _{gs} *8	$V_{GS} = 18V$	-	20	-	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	-	23	-	
Turn - on delay time	t _{d(on)} *8	$V_{DS} = 500V$	-	9.5	ı	
Rise time	t _r *8	$I_D = 29A$ $V_{GS} = +18V / 0V$	ı	22	ı	ns
Turn - off delay time	t _{d(off)} *8	$R_G = 6.8\Omega$, L = 250µH E_{on} includes diode	-	45	ı	115
Fall time	t _f *8	reverse recovery $L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF	ı	13	ı	
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	-	213	-	11.1
Turn - off switching loss	E _{off} *8		-	73	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vi} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values		Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_D = 29A$	-	3.3	-	V
Reverse recovery time	t _{rr} *8	$I_F = 29A$ $V_R = 500V$	ı	12	ı	ns
Reverse recovery charge	Q _{rr} *8	di/dt = 2700A/µs	ı	141	ı	nC
Peak reverse recovery current	I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	24	-	А

^{*1} Limited by maximum T_{vj} and for Max. R_{thJC}.

*5 Example of acceptable V_{GS} waveform



Please note especially when using driver source that V_{GSS_surge} must be in the range of absolute maximum rating.

- * 6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

^{*2} PW \leq 10µs, Duty cycle \leq 1%

^{*3} Only for body-diode, Repititive pulse, PW ≤ 500ns, Duty cycle ≤ 5%

^{*4} When used as a protective function, PW ≤ 10µs

Fig.1 Power Dissipation Derating Curve

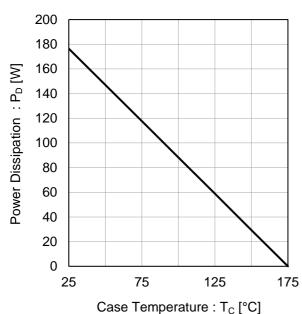


Fig.2 Maximum Safe Operating Area

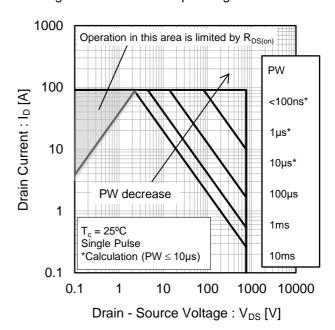
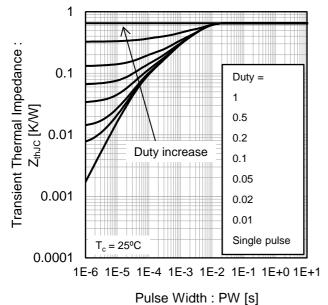
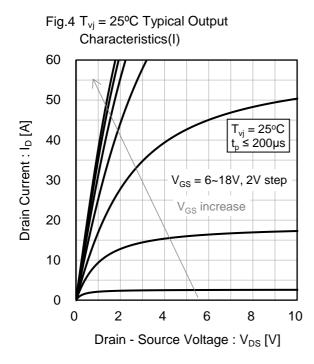


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



i disc viidiii . i vv [s]



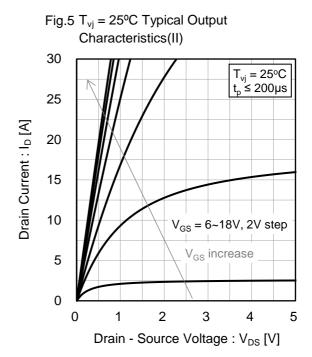
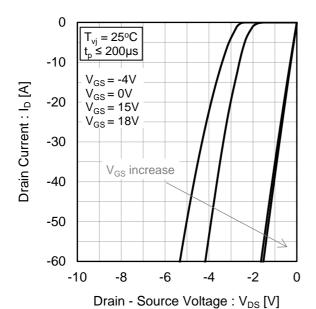


Fig.6 T_{vj} = 25°C 3rd Quadrant Characteristics



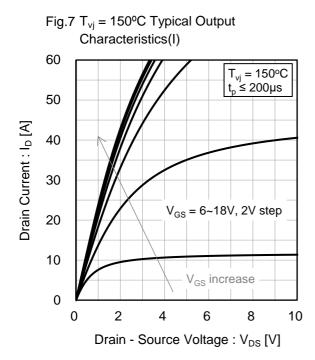
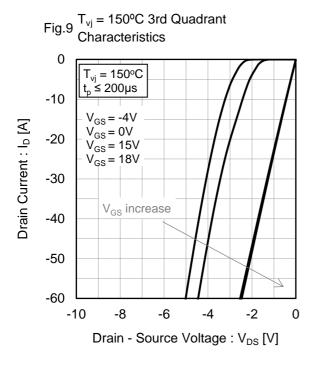
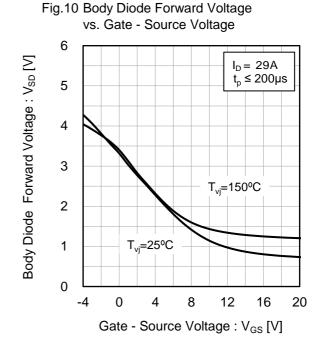


Fig.8 T_{vj} = 150°C Typical Output Characteristics(II) 30 $T_{vj} = 150^{\circ}C$ $t_p \le 200\mu s$ 25 Drain Current : I_D [A] 20 15 10 V_{GS} = 6~18V, 2V step 5 $V_{\rm GS}$ increase 0 0 1 3 5 Drain - Source Voltage: V_{DS} [V]





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Fig.11 Typical Transfer Characteristics (I)

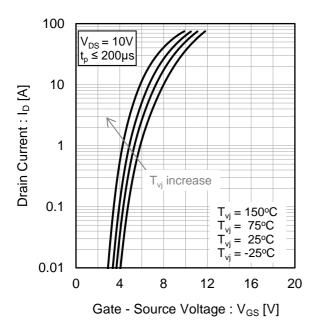


Fig.12 Typical Transfer Characteristics (II)

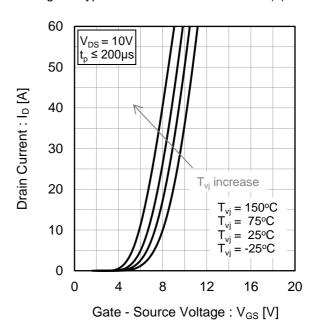


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

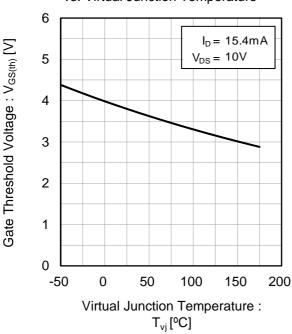
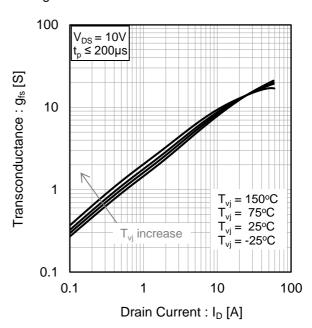
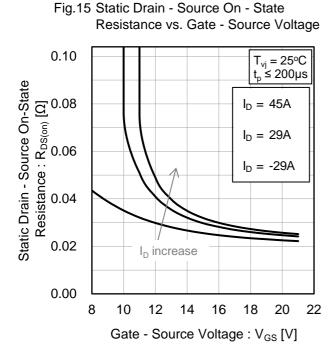


Fig.14 Transconductance vs. Drain Current





Resistance vs. Virtual Junction Temperature 0.10 $V_{GS} = 18V$ $t_p \le 200 \mu s$ Static Drain - Source On-State Resistance : R_{DS(on)} [Ω] 80.0 90.0 80.0 $I_D = 45A$ $I_{D} = 29A$ $I_D = -29A$ 0.02 I_D increase 0.00 -50 0 50 100 150 200 Virtual Junction Temperature: T_{vi} [°C]

Fig.16 Static Drain - Source On - State

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current T_{vi} = 150°C $T_{vj} = 125^{\circ}C$ Static Drain - Source On-State = 75°C = 25°C = -25°C Resistance : $R_{DS(on)}\left[\Omega\right]$ 0.1 0.01 T_{vi} increase $V_{GS} = 18V$ ≤ 200µs 0.001 10 100 Drain Current: ID [A]

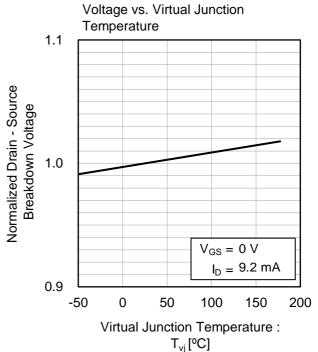
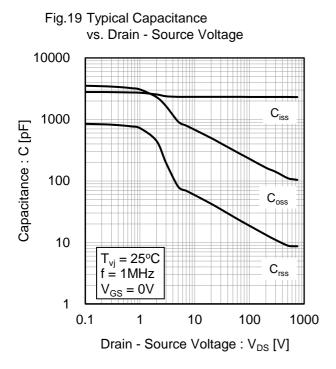


Fig.18 Normalized Drain - Source Breakdown



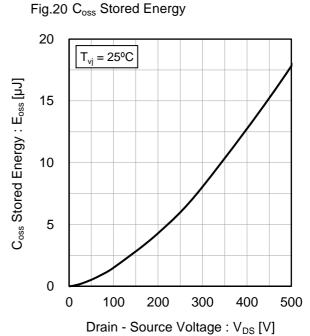


Fig.21 Dynamic Input Characteristics

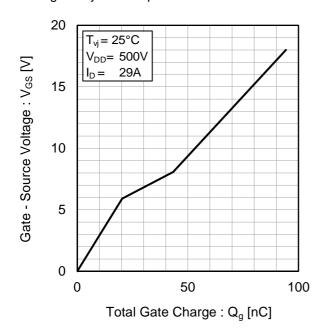
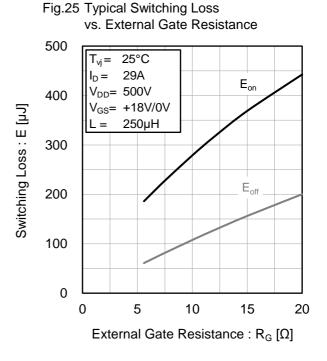


Fig.22 Typical Switching Time vs. External Gate Resistance 120 25°C 29A 100 $V_{DD} = 500V$ $t_{d(off)}$ V_{GS}= +18V/0V Switching Time : t [ns] 250µH 80 60 i t 40 20 0 5 0 10 15 20 External Gate Resistance : $R_G [\Omega]$

vs. Drain - Source Voltage 500 25°C 29A $I_D =$ V_{GS}= +18V/0V 400 Switching Loss: E [µJ] $R_G = 6.8\Omega$ 250µH L = 300 E_{on} 200 100 0 100 200 300 400 500 Drain - Source Voltage: V_{DS} [V]

Fig.23 Typical Switching Loss

Fig.24 Typical Switching Loss vs. Drain Current 500 25°C $T_{vj} =$ $V_{DD} = 500V$ 400 +18V/0V $V_{GS} =$ Switching Loss: E [µJ] $R_G =$ 6.8Ω E_{on} 250µH 300 $\mathsf{E}_{\mathrm{off}}$ 200 100 0 0 10 20 30 40 50 60 Drain Current: ID [A]



Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

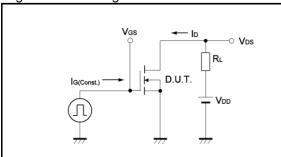


Fig.2-1 Switching Characteristics Measurement Circuit

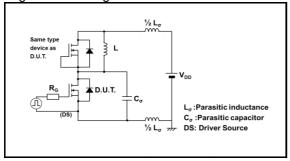


Fig.2-3 Waveforms for Switching Energy Loss

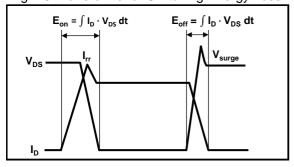


Fig.3-1 Reverse Recovery Time Measurement Circuit

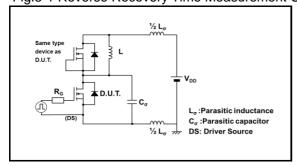


Fig.1-2 Gate Charge Waveform

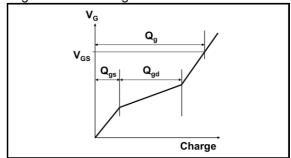


Fig.2-2 Waveforms for Switching Time

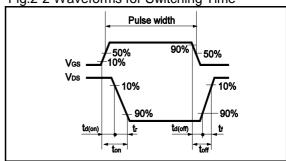
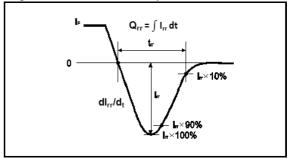
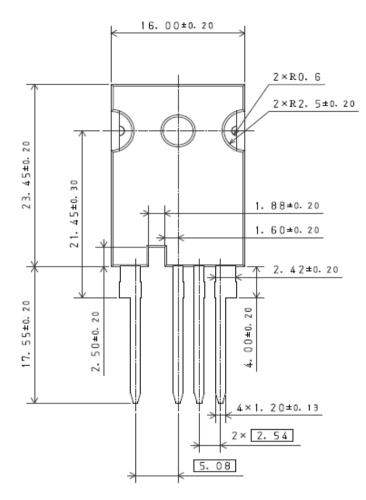
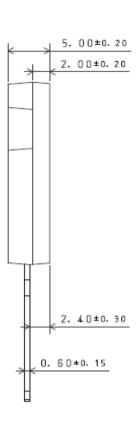


Fig.3-2 Reverse Recovery Waveform

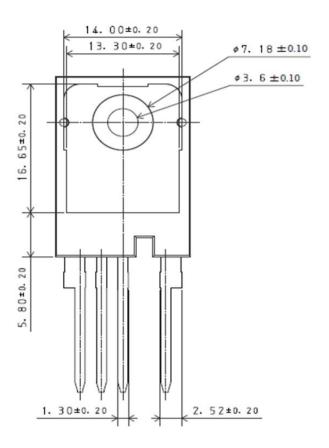


Package Dimensions



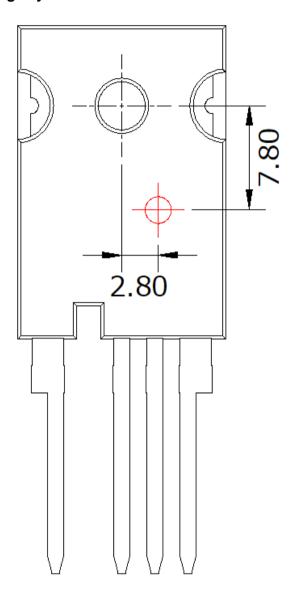


Unit: mm



Unit: mm

●Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- •If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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